Thermally Robust and Color-Tunable Blue-Green-Emitting 
BaMgSi$_4$O$_{10}$:Eu$^{2+}$,Mn$^{2+}$ Phosphor for Warm-White LEDs

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ABSTRACT: The dual emission produced from Mn$^{2+}$ when codoped with rare earth ions like Eu$^{2+}$ or Ce$^{3+}$ in inorganic compounds makes these materials attractive as efficient, color-tunable phosphors for warm-white solid-state lighting. Here, a series of efficient blue-green-emitting BaMgSi$_4$O$_{10}$:Eu$^{2+}$,Mn$^{2+}$ phosphors with thermally robust, tunable luminescence are reported. Steady-state and time-resolved photoluminescence spectroscopy reveal that Eu$^{2+}$ and Mn$^{2+}$ each occupy a single crystallographic site and confirm that energy transfer occurs from Eu$^{2+}$ to Mn$^{2+}$. The internal and external quantum efficiency of BaMgSi$_4$O$_{10}$:Eu$^{2+}$,Mn$^{2+}$ can reach as high as 69.0 and 47.5%, respectively, upon 360 nm excitation. Moreover, this phosphor possesses nearly zero-thermal quenching up to 440 K due to thermally induced electron detrapping. A fabricated UV-excited white LED device incorporating the blue-green-emitting BaMgSi$_4$O$_{10}$:Eu$^{2+}$,Mn$^{2+}$ and the red-emitting Sr$_2$Si$_5$N$_8$:Eu$^{2+}$ phosphors exhibits an excellent CRI of 94.3 with a correlated color temperature of 3967 K. These results prove the potential applications of Eu$^{2+}$,Mn$^{2+}$ codoped BaMgSi$_4$O$_{10}$ phosphor for generating warm-white light.

■ INTRODUCTION

The phosphor-converted white-light-emitting diode (pc-wLED) is an indispensable light source because of its high luminous efficacy, long operating lifetime, and environmentally benign components compared to incandescent and compact fluorescent light bulbs. One approach for constructing a pc-wLED is by using a near-UV (360−420 nm) LED chip as the excitation source in combination with three phosphors (red, green, and blue emitting materials). This has proven to be an excellent method for achieving a high color rendering index (CRI) and superior color uniformity in a warm-white light. However, this technology has high manufacturing costs partly because of the limited number of suitable phosphors available. Moreover, fluorescence reabsorption results in low luminous efficiency, and different aging rates of the phosphors cause the pc-wLED’s color to change over time. It is, therefore, necessary to produce new phosphors to tackle these issues.

The development of new phosphors with strong absorption in the UV region has recently focused on color-tunable materials where the emission covers a wide region of the visible spectrum. Co-doping is widely considered one of the most reliable strategies to create color-tunable phosphors. Energy transfer between doping ions can significantly promote the luminescent efficiency and color reproducibility as well as widen the emission spectra of phosphors. Typically, Ce$^{3+}$-Eu$^{2+}$ and Eu$^{2+}$/Ce$^{3+}$-Mn$^{2+}$ energy transfer are adopted to produce a broad blue-green or blue-red emission. Unfortunately, the emission color of these phosphors usually shifts as a function of temperature and shows a commensurate decrease in efficiency. This is likely because the two luminescent centers have different thermal quenching properties. In particular, Mn$^{2+}$ often suffers from severe thermal quenching. Thus, developing optically tunable phosphors with not only a highly efficient emission but also thermally robust luminescence is a significant challenge.

BaMgSi$_4$O$_{10}$ was first reported by Toropov et al. to crystallize in the tetragonal space group $P4/ncc$ and be isostructural with the mineral gillespite, shown in Figure 1a. The basic structural units in this original report include a [SiO$_4$] tetrahedron, a [BaO$_6$] dodecahedron, and a peculiar [MgO$_4$] square planar unit. However, the simulated X-ray diffraction pattern created using this structure model (shown in red in Figure 1b), does not completely match their

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experimental data (shown as the black data in Figure 1b). A similar conclusion is drawn in a brief study of BaMgSi4O10:Eu2+ as an inorganic phosphor, implying the wrong structure and incomplete experimental data for BaMgSi4O10 has been recorded in the database and that more work is needed to reveal the exact crystal structure of this compound. Nevertheless, the BaMgSi4O10:Eu2+ phosphor was reported to have an intense blue emission (centered at ~465 nm) and good thermal stability under ultraviolet excitation. However, a majority of the essential optical properties, such as particle morphology and quantum efficiency (QE) were not reported for this phosphor. Of greater interest is the fact that the Mg2+ site in the structure makes it suitable for Mn2+ doping because of their similarity in ionic size. Generally, Mn2+ presents a linear absorption in the ultraviolet to blue region due to the spin-forbidden 4T1-6A1 transition and exhibits green luminescence, including identifying the energy transfer and optical properties and potential for color-tunable photoluminescence. The BaMgSi4O10:Eu2+,Mn2+ phosphor was reported to exhibit a blue-green color-tunable character with nearly zero-thermal-quenching property for both the Eu2+ and Mn2+ emission centers, while maintaining a high quantum efficiency. Combining BaMgSi4O10:Eu2+,Mn2+ blue-green-emitting phosphor and Sr2Si2N2Eu2 red-emitting phosphor with a 370 nm LED chip produced a white-LED device with a high color rendering index (Ra) of 94.3 and a low correlated color temperature (CCT) of 3967 K, indicating the potential applications of this phosphor in near-UV-pumped warm white-LEDs.

RESULTS AND DISCUSSION

Synthesis, Phase, and Morphology. The synthesis of BaMgSi4O10 (BMSO) was first reported by Toropov et al., where the crystalline product was prepared from the prolonged crystallization of a BaMg2O2(SiO2)2 glass at 1223 K. Analyzing the standard card (PDF no. 15-0182) in crystal structure databases and comparing these data to the experimental X-ray diffractionogram suggests an incomplete crystal structure solution. Despite this, Inoue et al. synthesized an Eu2+-substituted BaMgSi4O10 (BMSO:Eu2+) phosphor by sintering the powder twice at 1373 K. These samples showed an intense diffraction peak near 2θ = 30°, which was ascribed to the product, but it is not in the original report by Toropov et al. Yuan et al. also synthesized BMSO:Eu2+ and this sample matched the original standard card. This synthesis involved a two-step reaction of sintering at 1273 and 1473 K. Considering the significant

EXPERIMENTAL METHODS

Synthesis. (Ba1-xEu)x(Mg1-xMnx)Si4O10 (x = 0, 0.04; y = 0, 0.02, 0.04, 0.06, 0.08, 0.1, and 0.12) was prepared by conventional high-temperature solid-state reaction using BaCO3 (Aldrich, 99.99%), 4MgCO3·Mg(OH)2·3H2O (Aldrich, 99.9%), SiO2 (Aldrich, 99.95%), MnCO3 (Aldrich, 99.9%), and Eu2O3 (Aldrich, 99.99%) as the starting materials. The starting materials were first weighed out according to the required stoichiometric ratio, and then mixed thoroughly using a shaker mill (Spex 8000M) in a polystyrene vial with two methacrylate balls (Φ = 9.5 mm) as grinding media for 30 min. The homogeneous mixtures were subsequently placed in a graphite crucible and heated at 1353 K for 12 h under a reducing atmosphere (5% H2/95% N2) using a heating and cooling rate of 3 K/min. The final product was ground into a fine powder using an agate mortar and pestle.

Characterization. X-ray diffractograms were collected on an XPert3 PANalytical (Cu Kα, λ = 1.5406 Å) equipped with an Anton-Paar TTK450 temperature chamber. The scanning electron micrographs (SEM) and energy-dispersive spectroscopy (EDS) maps were collected on a Hitachi-S4800 (Japan). The room-temperature and temperature-dependent photoluminescence spectra were recorded using a PTI QuantaMaster with a 75 W xenon arc lamp for excitation and a Janis cryostat (VFP-100) to control the temperature between 80 and 500 K. The time-gated photoluminescence decay measurements of Eu2+-doped samples were collected using a Horiba DeltaFlex Lifetime System. The decay curves of Mn2+-doped samples were collected using an FLS-980 fluorescence spectrophotometer (Edin-burgh Instruments) equipped with a xenon flash lamp (450 W, Osram) as the excitation source. The internal and external quantum efficiency (QE) were measured using the integrating sphere on the QE-2100 quantum yield measurement system (Otsuka Electronics Co., Ltd., Japan), and a Xe lamp as the excitation source with BaSO4 powder as a reference. The thermoluminescence (TL) curves were collected by a thermoluminescence meter (SL08-L, Guangzhou-Radiation Science and Technology Co. Ltd.) with the heating rate of 1 K/s after being excited for 5 min under 254 nm lamp. The diffuse reflection (DR) spectra were detected on a UV-vis-NIR spectrophotometer (SHIMADZU, Japan) with an integrated sphere attachment and BaSO4 powder as a standard. The pc-LED device was fabricated by using a 370 nm LED combined with a phosphor “cap”, which was prepared by curing an intimate mixture of Ba5Eu4Mg17Mn2Si10O31y·lab-made Sr2Si2N2Eu2+, and a transparent silicone resin (GE Silicones, RTV615) in a custom brass mold. The electroluminescence spectrum, CRI, and CCT of the pc-LED device were measured under a forward bias of 20 mA using an AvaFast fiber optic Vis/NIR spectrometer coupled to a 50 mm integrating sphere.

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Figure 1. (a) Crystal structure of BaMgSi4O10 with the proposed gillespite structure; (b) original reported experimental powder X-ray diffractogram of BaMgSi4O10 compared with a simulated diffractogram of the gillespite structure taken from the International Centre for Diffraction Data (ICDD) database.
differences in crystal structure stemming from the sintering temperatures in previous work, here, we systematically investigated the relationship between phase formation and reaction temperature. The optimized sintering temperature to prepare a phase-pure sample was found to be 1353 K. This route produced single-phase \( \text{BaMgSi}_4\text{O}_{10} \) identical to the sample presented by Inoue et al. Interestingly, sintering above 1373 K causes the samples to melt, and sintering below 1343 K results in \( \text{BaSi}_2\text{O}_5 \) impurity. The product prepared at 1353 K can be confidently claimed to be single phase. This is because numerous adjustments to the reaction conditions including temperature, adding flux, multistep sintering, and pressing a pellet of the raw powder before heating resulted in a powder pattern that contained the diffraction peak near 30°. More importantly, the relative intensity of peaks never changed in all of these samples. Thus, this corroborates the work by Inoue et al., where the diffraction peak near 30° indeed belongs to \( \text{BMSO} \).

\( \text{BMSO}:\text{Eu}^{2+} \) and the \( \text{Mn}^{2+} \)-substituted \( \text{BaMgSi}_4\text{O}_{10} \) (\( \text{BMSO}:\text{Mn}^{2+} \)) phosphors were subsequently synthesized at 1353 K. Additionally, a series of \( \text{Ba}_{1-x}\text{Eu}_{x}\text{Mg}_{1-y}\text{Mn}_{y}\text{Si}_4\text{O}_{10} \) (\( \text{BMSO}:\text{Eu}^{2+},\text{Mn}^{2+} \)) were also produced. The X-ray diffraction patterns of these samples (presented as Figure 2) show excellent agreement with the compounds reported by Inoue et al.\(^3\) No other phases could be indexed, indicating that no impurities and structural variations occur upon doping. Unfortunately, solving the structure from powder X-ray diffraction is nearly impossible because of the random orientation of the crystals. The most reliable way to determine the crystal structure is through single-crystal diffraction. The particle size of these samples is only tens of micrometers, which is too small to obtain a dependable single-crystal pattern. Thus, an exact structure solution remains elusive, and additional work is needed to grow larger single crystals to solve this compound’s structural uncertainty.

Analyzing the morphology of synthesized \( \text{Ba}_{0.96}\text{Eu}_{0.04}\text{Mg}_{0.96}\text{Mn}_{0.04}\text{Si}_4\text{O}_{10} \) sample using SEM (Figure 3a) shows that all of the particles are irregular in shape with a size of 10 to 20 \( \mu \)m. EDS mapping (shown in Figure 3b–h) indicates that the elements Ba, Mg, Si, Eu, and Mn contained in this sample are homogeneously distributed within a single particle.

Diffuse Reflection Spectra and Photoluminescence Properties. The diffuse reflection spectra of \( \text{BMSO} \), \( \text{BMSO}:\text{Eu}^{2+} \), and \( \text{BMSO}:\text{Eu}^{2+},\text{Mn}^{2+} \) were examined (Figure 4a–c). \( \text{BMSO}:\text{Eu}^{2+} \) and \( \text{BMSO}:\text{Eu}^{2+},\text{Mn}^{2+} \) both present an intense absorption in the UV and near-UV region (250–420 nm), which can be ascribed to the \( 4f^7 \rightarrow 4f^65d^1 \) transitions of the Eu\(^{2+} \) ions. The absorption cutoff edge of the host is \( \sim \)288 nm, and the optical band gap \( (E_g) \) can be estimated to be 4.3 eV based on the data plotted in Figure 4d.
The photoluminescent excitation and emission of BMSO:Eu$^{2+}$ were measured and are plotted in Figure 5a.

![Figure 5](https://dx.doi.org/10.1021/acs.inorgchem.0c01803)

**Figure 5.** (a) Photoluminescent excitation spectra monitored at different emission wavelengths ($\lambda_{em} = 430–500$ nm) and emission spectra with different excitations ($\lambda_{ex} = 260–390$ nm) of BMSO:0.04Eu$^{2+}$ sample; (b) the corresponding normalized excitation and emission spectra; (c) Gaussian fitting emission spectrum of BMSO:0.04Eu$^{2+}$ excited by 360 nm; (d) room-temperature excitation and emission spectra of BMSO:0.04Eu$^{2+}$, BMSO:0.08Mn$^{2+}$ and BMSO:0.04Eu$^{2+}$, 0.04Mn$^{2+}$ phosphor.

These data show that this phosphor exhibits a blue emission with the peak centered at 464 nm upon UV excitation. The excitation spectrum ($\lambda_{em} = 464$ nm) covers a broad range from 250 to 400 nm, following previous reports.\(^{30,31}\) Noticeably, the normalized emission spectra (Figure 5b) with different excitations varying from 260 to 390 nm overlap, indicating a large possibility of single emission center in this sample and further supports a structure solution with a single crystallographic Ba$^{2+}$ site in BMSO. Additionally, the normalized excitation spectra of BMSO:Eu$^{2+}$ monitored at different emission wavelengths ranging from 430 to 500 nm also nearly overlap, further confirming that the broad emission of Eu$^{2+}$ in BMSO is derived from different vibrational levels of a single emission center.\(^{33}\) Moreover, the emission spectrum excited by 360 nm can be well fitted by a single Gaussian band (shown in Figure 5c), which is direct evidence for Eu$^{2+}$ substituting a single crystallographic Ba$^{2+}$ site in BMSO.

Analyzing the Mn$^{2+}$-doped BaMgSi$_4$O$_{10}$ (BMSO:Mn$^{2+}$) sample presents a weak yellow-green emission peak centered at 537 nm (Figure 5d), suggesting Mn$^{2+}$ occupies a four-coordinated Mg$^{2+}$ site. Considering the considerable overlap between the excitation band of BMSO:Mn$^{2+}$ and the emission band of BMSO:Eu$^{2+}$, an effective resonance energy transfer in the BMSO:Eu$^{2+}$:Mn$^{2+}$ phosphor is expected. Fixing the Eu$^{2+}$ concentration at $x = 0.04$ and then gradually increasing the Mn$^{2+}$ concentration ($y = 0.02–0.12$) causes the emission contribution from Eu$^{2+}$ at 464 nm to decrease, whereas the emission intensity of Mn$^{2+}$ at 537 nm increases (Figure 6). This occurs until the concentration quenching limit at $y = 0.1$. As a result, this series of phosphors exhibit intense, tunable emission from blue to yellow-green as a function of Mn$^{2+}$ concentration (illustrated as inset of Figure 6). Interestingly, the normalized excitation spectra of the Eu$^{2+}$-doped sample ($\lambda_{em} = 464$ nm) and the Eu$^{2+}$-Mn$^{2+}$ codoped samples ($\lambda_{em} = 537$ nm) show no difference, indicating most of the emission energies of Mn$^{2+}$ originates from Eu$^{2+}$ absorption followed by energy transfer.

**Energy Transfer Mechanism.** Time-gated photoluminescence decay curves were collected (plotted in Figure 7) to investigate the energy transfer process. The decay curve of Eu$^{2+}$ in BaMgSi$_4$O$_{10}$ can be fit to a single exponential function (shown as Figure 7a), supporting the idea that only one Eu$^{2+}$ emission center is present in the crystal structure. However, the decay curves of Eu$^{2+}$ in Ba$_{1−x}$Eu$_x$Mg$_{0.96}$Mn$_{0.04}$Si$_4$O$_{10}$ ($x = 0.04; y = 0–0.12$) samples deviate from the single exponential function, and the lifetime decreases gradually from 1.48 to 1.14 $\mu$s with increasing $y$, due to the energy transfer from Eu$^{2+}$ to Mn$^{2+}$. The decay curve of Mn$^{2+}$ (depicted as Figure 7c) in the Eu$^{2+}$-Mn$^{2+}$ codoped phosphor system also exhibits a single exponential character, indicating only one type of Mg$^{2+}$ site available for Mn$^{2+}$.

The energy transfer efficiency, $\eta_T$, from Eu$^{2+}$ to Mn$^{2+}$ can be calculated based on the lifetimes of Eu$^{2+}$ with the following equation:\(^{34}\)
respectively. The relationships between \( \eta \) values of Eu\(^{2+} \) in the absence and presence of Mn\(^{2+} \), respectively. The energy transfer efficiency, \( \eta_{ET} \), as a function of Mn\(^{2+} \) doping concentration is given in Figure 8a. As shown, \( \eta_{ET} \) gradually increases with increasing Mn\(^{2+} \) concentration and reaches an efficiency of \( \sim 30\% \) with 12 mol \% Mn\(^{2+} \) doping concentration. This relatively low value of \( \eta_{ET} \) implies that a small part of the energy absorbed by Eu\(^{2+} \) ions is assigned to Mn\(^{2+} \). A similar situation can also be found in Ce\(^{3+-Mn^{2+} \) codoped \( \gamma \)-AlON phosphor.\(^{35} \) The \( \eta_{ET} \) is possible to be further increased by increasing Mn\(^{2+} \) doping concentration, but the increasing concentration quenching of Mn\(^{2+} \) may result in low emission efficiency as well.

Generally, the energy transfer mechanisms are exchange interactions and electric multipolar interactions. According to Dexter’s energy transfer theory and Reisfeld’s approximation, the interactions can be determined by the following equations:

\[
\ln \frac{\eta_0}{\eta_i} \propto C_{Eu^{2+}+Mn^{2+}} \quad \text{and} \quad \frac{\eta_0}{\eta_i} \propto C^{\frac{3}{2}}_{Eu^{2+}+Mn^{2+}}
\]

where \( \eta_0 \) and \( \eta_i \) are the luminescence quantum efficiencies of Eu\(^{2+} \) in the absence and presence of Mn\(^{2+} \), respectively. The values of \( \eta_0/\eta_i \) can be estimated approximately by the ratio of relative luminescence intensity ratio \( I_{0}/I_i \) (shown as Figure 8b) and \( C \) is the sum of the concentrations of Eu\(^{2+} \) and Mn\(^{2+} \).

Finally, a proportional relationship between \( \ln (I_{0}/I_i) \) and \( C_{(Eu^{2+}+Mn^{2+})} \) corresponds to exchange interaction, whereas the relationship \( I_{0}/I_i \) versus \( C^{3/2} \) \( (Eu^{2+}+Mn^{2+}) \) with \( n = 6, 8, \) and 10 correspond to dipole–dipole \( (d-d) \), dipole–quadrupole \( (d-q) \), and quadrupole–quadrupole \( (q-q) \) interactions, respectively.\(^{39} \) The relationships between \( I_{0}/I_i \) and \( C^{3/2} \) \( (Eu^{2+}+Mn^{2+}) \) are depicted in Figure 8c, d. As presented, the best linear behavior evaluated through comparing the fitting factor, \( R^2 \), is observed only when \( n = 6 \), implying that energy transfer from Eu\(^{2+} \) to Mn\(^{2+} \) occurs via the dipole–dipole mechanism.

**Temperature-Dependent Photoluminescence.** Thermal stability is a key criterion that should be evaluated for any practical phosphor application.\(^{41,42} \) The emission spectra of the BaMgSi\(_2\)O\(_4\):0.04Eu\(^{2+} \) and BaMgSi\(_2\)O\(_4\):0.04Eu\(^{2+} \),0.04Mn\(^{2+} \) phosphors excited by 360 nm near-ultraviolet light were investigated from 80 to 520 K. As shown in Figure 9, the relative emission intensity of BaMgSi\(_2\)O\(_4\):0.04Eu\(^{2+} \) is found to decrease slightly with increasing temperature reaching a minimum at 200 K, followed by an increase, reaching the maximum at 260 K. The emission is then stable until 440 K and finally decreases with further heating. Fortunately, there is minimal thermal quenching in the temperature range from 300 to 440 K, which is usually the operating temperature for LED devices, making this phosphor viable for application in LED-based light bulbs. Also, the Eu\(^{2+} \) in BaMgSi\(_2\)O\(_4\):0.04Eu\(^{2+} \),0.04Mn\(^{2+} \) phosphor possesses an outstanding thermal performance, similar to that in the BaMgSi\(_2\)O\(_4\):0.04Eu\(^{2+} \) phosphor. However, the Mn\(^{2+} \) presents the same trend in emission intensity but has a surprisingly better thermal performance than the Eu\(^{2+} \) in BaMgSi\(_2\)O\(_4\):0.04Eu\(^{2+} \),0.04Mn\(^{2+} \) phosphor. This indicates that the energy transfer efficiency (\( \eta_{ET} \)) is not changed as the temperature varies and that the Mn\(^{2+} \) luminescence in this codoped phosphor has high thermal stability, which is rare. Moreover, the emission peak from Mn\(^{2+} \) broadens without a shift in emission wavelength, whereas the Eu\(^{2+} \) emission also broadens with a gradual blue-shift (\( \sim 10 \) nm) in the measured temperature range.

Two traditional models can explain thermal quenching process, i.e., crossing relaxation and thermal ionization.\(^{43,44} \) Crossing relaxation can be characterized by the activation energy for thermal quenching, \( E_a \) which is experimentally obtained by fitting the temperature-dependent emission data to the Arrhenius equation. Thermal ionization can be characterized by \( E_{ai} \) the energy difference between the highest 5d level and the bottom of the conduction band, which usually occurs in phosphor systems with a narrow band gap.\(^{41,45} \) However, our experimental thermal quenching measurements inferred that both of these models could not be applied to this phosphor system because of the complex variations of emission intensity as a function of temperature. Recently, a defect-related model was proposed to interpret the increase in
emission intensity with increasing temperature. This model states that electrons detrapping from defect states can compensate for the emission intensity loss caused by thermal quenching. The zero-thermal quenching property in phosphors such as Na₃Sc₂(PO₄)₃:Eu²⁺ and K₂BaCa(PO₄)₂:Eu²⁺ can be explained with this model. To support the existence of defects in our phosphor, we collected the thermoluminescence (TL) spectra of BaMgSi₄O₁₀:0.04Eu²⁺ and BaMgSi₄O₁₀:0.04Eu²⁺,0.04Mn²⁺ in the temperature range of 300−780 K after being excited with 254 nm ultraviolet light for 5 min (Figure 10). As presented, the TL curve of BaMg-

![](image)

Figure 10. TL curves and Gaussian deconvolutions of (a) BaMgSi₄O₁₀:0.04Eu²⁺, and (b) BaMgSi₄O₁₀:0.04Eu²⁺,0.04Mn²⁺ phosphor collected in the temperature range of 300−780 K.

Si₄O₁₀:0.04Eu²⁺ shows a wide distribution that can be well fitted with three Gaussian bands centered at 351, 409, and 520 K, corresponding to trap depths of 0.70, 0.82, and 1.04 eV, respectively. These values are estimates obtained from the rough relationship \(E_T = T/500\) eV, where \(T\) is the temperature in kelvin (K). Moreover, the trap depths in the Eu²⁺-Mn²⁺ codoped sample are the same as Eu²⁺ doped sample, but the concentration of each kind of defect is different. To fully understand the mechanism of thermally induced electron detrapping, a complete structure solution for this phosphor is still necessary, which will be the goal of our future work.

Quantum Efficiency and CIE Coordinates. A previous report indicated BMSO:Eu²⁺ has high emission efficiency under 310 nm excitation, being comparable with that of YAG:Ce³⁺ excited by 460 nm; however, the quantum efficiency under near-UV excitation remains unknown. To further evaluate the practical use of this phosphor, we measured the internal and external quantum efficiency (IQE, EQE) and CIE coordinates of Ba₁₋ₓEuₓMg₁₋₂Mn₂⁺Si₄O₁₀ (\(x = 0\) or 0.04, \(y = 0−0.12\) named no. 1−7; \(x = 0, y = 0.08\) named no. 8) upon 360 nm excitation and presented them in Figure 11a, b. The IQE and EQE of BaMgSi₄O₁₀:0.04Eu²⁺ was determined to be 75.3 and 51.7%, respectively, whereas in the Eu²⁺-Mn²⁺ codoped BaMgSi₄O₁₀ system, the IQE and EQE first increases and then decreases with increasing Mn²⁺ concentration and reaches a maximum of 69.0 and 47.5%, respectively, when \(x = y = 0.04\). For comparison, the IQE and EQE values of the commercial blue phosphor BAM:Eu²⁺ was measured to be 92 and 71%, respectively, under 360 nm excitation. Thus, further synthetic optimization is still necessary to promote the QE. The CIE chromaticity coordinates of this phosphor system can be tuned from blue (0.162, 0.168) to yellow-green (0.341, 0.610) shown in Figure 11c, and demonstrates that this phosphor system has a highly tunable emission with a sufficient quantum efficiency.

**Application in Near-UV pc-wLEDs.** To evaluate the device performance of the Eu²⁺-Mn²⁺ codoped BaMgSi₄O₁₀ phosphor, we fabricated a pc-wLED using BaMgSi₄O₁₀:0.04Eu²⁺,0.04Mn²⁺ as the blue-green-emitting phosphor, Sr₂Si₅N₈:Eu²⁺ as the red-emitting phosphor, and a 370 nm NUV chip as the excitation source. This combination of phosphors and LED chip, shown in Figure 12a, generates a warm white light with CIE coordinate of (0.384, 0.383) driven by a 20 mA current (Figure 12b) giving it an acceptable color correlated temperature (CCT = 3967 K) and a high corresponding color rendering index (Ra = 94.3). These results indicate that the Eu²⁺-Mn²⁺ codoped BaMgSi₄O₁₀ phosphor is an efficient blue-green-emitting phosphor and

![](image)

Figure 11. (a) QE measurement of BMSO:Eu²⁺ phosphor; (b) IQE and EQE of Ba₁₋ₓEuₓMg₁₋₂Mn₂⁺Si₄O₁₀ (\(x = 0.04, y = 0−0.12\) named no. 1−7; \(x = 0, y = 0.08\) named no. 8); and (c) the corresponding CIE chromaticity coordinates.

![](image)

Figure 12. (a) Emission spectrum of a white LED fabricated by BaMgSi₄O₁₀:0.04Eu²⁺,0.04Mn²⁺, Sr₂Si₅N₈:Eu²⁺, and a 370 nm LED chip; the inset is the photograph of the white LED under a forward bias of 20 mA. (b) CIE coordinates of the fabricated white LED.
may be combined with other red phosphors to achieve high-quality UV-excited warm-white pc-LEDs.

**CONCLUSIONS**

In summary, a series of Eu²⁺-Mn²⁺ codoped BaMgSi₄O₁₀ phosphors were synthesized by conventional high-temperature solid-state reactions. Steady-state and time-resolved photoluminescence spectroscopy indicate that energy transfer occurs from Eu²⁺ to Mn²⁺ through dipole–dipole interactions. Upon 360 nm excitation, the internal and external quantum efficiency of the codoped phosphor reached 69.0 and 47.5%, respectively, and the phosphor shows negligible thermal quenching up to 500 K. The origin of the impressive temperature-dependent properties can be ascribed to thermally released electrons trapped by defects to the 5d Eu²⁺ orbitals. Finally, a NUV-excited (λ_ex = 370 nm) pc-wLED device with a CCT = 3967 K and Ra = 94.3 was fabricated by combining the blue-green-emitting BaMgSi₄O₁₀:0.04Eu²⁺-0.04Mn²⁺ phosphor with red-emitting Sr₂Si₅N₈:Eu²⁺, demonstrating the potential applications of Eu²⁺-Mn²⁺ codoped BaMgSi₄O₁₀ phosphor in pc-wLEDs.

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**Notes**

The authors declare no competing financial interest.

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**REFERENCES**


(8) Li, G.; Tian, Y.; Zhao, Y.; Lin, J. Recent Progress in Luminescence Tuning of Ce³⁺ and Eu³⁺-Activated Phosphors for Pc-WLEDs. Chem. Soc. Rev. 2015, 44 (23), 8688–8713.


(10) Sun, L.; Devakumar, B.; Liang, J.; Wang, S.; Sun, Q.; Huang, X. Highly Efficient Ce³⁺ → Tβ⁺ Energy Transfer Induced Bright Narrowband Green Emissions from Garnet-Type Ca₂Y₂Zr₂(AlO₄)₃:Ce³⁺, Tβ⁺ Phosphors for White LEDs with High Color Rendering Index. J. Mater. Chem. C 2019, 7 (34), 10471–10480.


